

# ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

Stylesheet Version v18.0

Title of Invention	MAGNETIC RANDOM ACCESS MEMORY AND METHOD OF FABRICATING THEREOF
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Application Number : 10/604533

Confirmation Number: 7-29-03

First Named Applicant: William Wille

Attorney Docket Number: FIS920020132US1

Art Unit: 2813

Examiner:

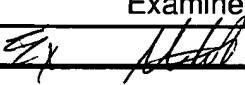
Search string: ( 5695810 or 5804458 or 5920500 or 5936293 or 6147900 or 6165803 or 6351408 or 6365419 or 6381170 or 6396735 or 6048739 ).pn

## US Patent Documents

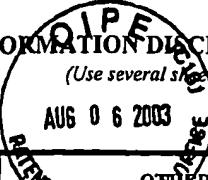
Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite. No.	Patent No.	Date	Patentee	Kind	Class	Subclass
1	5695810	1997-12-09	Dubin, et al.				
2	5804458	1998-09-08	Tehrani, et al.				
3	5920500	1999-07-06	Tehrani, et al.				
4	5936293	1999-08-10	Parkin				
5	6147900	2000-11-14	Pohm				
6	6165803	2000-12-26	Chen, et al.				
7	6351408	2002-02-26	Schwarzl, et al.				
8	6365419	2002-04-02	Durlam, et al.				
9	6381170	2002-04-30	Prinz				
10	6396735	2002-05-28	Michijima, et al.				
11	6048739	2000-04-11	Hurst, et al.				

Signature

Examiner Name	Date
	12/10/04

**EXAMINER:** Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<b>INFORMATION DISCLOSURE CITATION</b> <i>(Use several sheets if necessary)</i>		Docket Number (Optional) <b>FIS920020132US1</b>	Application Number <b>NYA</b>
 <b>AUG 06 2003</b>		Applicant(s) <b>NUETZEL ET AL.</b>	
		Filing Date <b>NYA</b>	Group Art Unit <b>NYA</b>
*EXAMINER INITIAL <i>JMM</i>	<b>OTHER DOCUMENTS</b> <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>		
	3	L.A. D'Asaro, J. V. DiLorenzo, and H. Fukui; "Improved Performance of GaAs Microwave Field-Effect Transistors with Low Inductance Via Connections Through the Substrate;" IEEE Transactions on Electron Devices, Vol. ED-25, No. 10, October 1978; pages 1218 - 1221.	
	4	T. Ishikawa, K. Okaniwa, M. Komaru, K. Kosaki, and Y. Mitsui; "A High-Power GaAs FET Having Buried Plated Heat Sink for High-Performance MMIC's" IEEE Transactions on Electron Devices, Vol. 41, No. 1; January 1994; pages 3 - 9	
EXAMINER <i>Ex Mather</i>	DATE CONSIDERED <i>02/11/04</i>		

\*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.